Deep-level transient spectroscopy of TiO$_2$/CuInS$_2$ heterojunctions

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Deep-level transient spectroscopy (DLTS) has been used to measure the concentration and energy position of deep electronic states in CuInS$_2$. Flat TiO$_2$/CuInS$_2$ heterojunctions as well as TiO$_2$-CuInS$_2$ nanocomposites have been investigated. Subband-gap electronic states in CuInS$_2$ films are mostly due to antisite point defects and vacancies. Substitution of indium with copper, CuIn$_n^\text{II}$, leads to an acceptor state 0.15 eV above the valence band, while copper vacancies, V$_\text{Cu}^\text{V}$, are acceptor states at 0.1 eV. Furthermore, indium on a copper position, In$_\text{Cu}$, yields a donor state at 0.07 eV below the conduction band, while sulphur vacancies are donor states at 0.0 eV. With DLTS, these states are indeed found. For flat configurations, V$_\text{Cu}^\text{V}$ are the dominant acceptors with a concentration of $1.83 \times 10^{17}$ cm$^{-3}$. In contrast for nanocomposites CuIn$_n^\text{II}$ are the dominant acceptors having a concentration of $6.7 \times 10^{17}$ cm$^{-3}$. We conclude that the concentration of antisite defects in nanocomposite CuInS$_2$ is significantly higher than that in flat films of CuInS$_2$.© 2005 American Institute of Physics. [DOI: 10.1063/1.2140611]

In recent years, solar cell technology—based on the ternary compound semiconductors, such as CuInSe$_2$, CuGaSe$_2$, CuInS$_2$, and their multinary alloys Cu(In,Ga)$_\times$-(Se,S)$_{1-x}$—have been advanced.$^\text{1–4}$ Within this family, CuInS$_2$ is considered a promising candidate because of its high absorption coefficient and its direct band gap of $E_p = 1.5$ eV, which is well matched to the solar spectrum.$^\text{5}$ Natural defects, introduce energy levels in the band gap of CIS which leads to recombination.$^\text{6}$ Indeed, a correlation between the density of a deep bulk states and the open-circuit voltage is:

$$C(t) = C_0 + \Delta C \exp[-t/\tau],$$

where $\tau$ is the decay time, $e_p$, of the released charges, $C_0$ is the capacitance prior to the filling pulse, and $\Delta C$ represent the difference between the capacitance at the beginning and at the end of the filling pulse.

The explicit form of the time dependence of the capacitance is:

$$e_p = 1/\tau_p \gamma T^2 \sigma_{pa} \exp(-E_{pa}/kT),$$

where $\sigma_{pa}$ is the capture cross section, $\gamma$ is a constant equal to $3.25 \times 10^{21} (m_p/m_0)$, where $m_p$ is the effective hole mass being 1.3 $m_0$. $E_{pa}$ is the thermal activation energy, $k$ is the Boltzmann constant, and $T$ is the temperature. A plot of $\ln(\tau \gamma T^2)$ versus $(1/T)$ yields a straight line with a slope of $(E_{pa}/k)$, from which the energy of the involved electronic state can be determined. In addition, the $y$-axis intercept of $\ln(1/\gamma \sigma_{pa})$ yields to the capture cross section.

Furthermore, the trap density $N_t$ can be calculated using the following expression:

$$N_t = N_A(\Delta C/C_0).$$

The effective acceptor density can be determined from capacitance-voltage measurements.

In the present study, DLTS is performed in a temperature interval from 130 to 400 K. Capacitance transients are mea-

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sured up to 30 s after the filling pulse is applied. The filling pulse duration width is in the range of 0.1–10 s, with a bias voltage limited to approximately −1 V.

Figure 1 shows two representative capacitance transients recorded after a filling pulse of 0.5 V from −0.6 to −0.1 V. Before and after the filling pulse, a constant bias voltage of −0.6 V is maintained. The modulation frequency is varied between 1 Hz and 1 MHz. Upon applying this filling pulse, both minority and majority carriers are injected in CuInS2 by which the occupation of deep acceptor and donor states are changed. From the temperature dependence of the capacitance transients, we determine the activation energies of the depopulation process. A value of 0.107 eV is found for the majority carriers while 0.04 eV is obtained for the minority carriers.12

The duration of the filling pulse does not influence the recorded DLTS data; when the pulse time is varied from 0.03 s to 10 s, no changes in the thermal activation energy are found. This suggests that the trap centers can be considered to be isolated points defects and that the energy distribution of the electronic states is small. On the other hand, the modulation frequency does have a significant influence on the DLTS signal. As is shown in Fig. 1, for frequencies higher than 500 kHz the minority carrier-type DLTS signal is recorded, while at frequencies between 0.5 Hz and 10 kHz majority type signals are found. Within these frequency windows, the activation energies that are derived have an insignificant frequency dependency. These results are different then the ones reported by Siemer et al.,13 which may be due to differences in the preparation of CuInS2. In dense CuInS2 deposited by ALD, the predominant defects appear to be related to copper and sulphur vacancies. The presence of a deeper state could not be found, which suggests that for flat films the concentrations of deeper states related to Cu–Au order, i.e., CuInII and InCuIII, have relatively low concentrations.

ALD is a self-limiting method allowing layer-by-layer growth to yield conformal deposition on textured surfaces. One could thus expect that the same quality of the absorber semiconductor can be obtained for flat and three-dimensional (3D) devices. However, although the same deposition parameters have been used for the deposition of CuInS2 inside nanoporous TiO2 and onto dense TiO2, different properties are obtained for the two cases. CIS thin films grown with atomic layer-chemical vapor deposition are p-type semiconductors, due to the presence of copper ion vacancies VCuI, indium ion vacancies ViII, and antisite acceptor defects CuInIII, which are charge compensated by holes. If deviation from stoichiometry is small, CuInII antisite defects are accompanied by a donor antisite defect InCuIII. The presence of these antisite defects is not significant at room temperature, as the majority carrier activation energy is below the Fermi level. As the temperature is increased, the density of occupied deep acceptor states is increased, and the energy of the occupied states is raised. At temperatures above 500 K, the occupation of deep acceptor states is observed, and the activation energy of the depopulation process is found to be 0.107 eV for the majority carriers.

![Graph of capacitance transients](image)

**FIG. 2.** Activation energy of minority (a) and majority (b) charge traps in the subband gap of CuInS2 that form flat heterojunctions.
defects is related to the occurrence of Cu–Au ordering. The degree of the Cu–Au ordering is larger for CuInS$_2$ deposited into the nanostructured TiO$_2$ matrix than when CuInS$_2$ is deposited on dense substrates, as has been discussed in previous studies.$^{14,15}$

Similar to the flat film configuration, the majority type signal in nanocomposites is recorded at low modulation frequencies, while the minority type is recorded at high modulation frequencies [Figs. 1(a) and 1(b)]. The thermal activation energy of electron traps in the nanocomposite CuInS$_2$ is found to be 0.07 eV [Fig. 3(b)], while the activation energies for hole traps are 0.1 eV and 0.155 eV [Fig. 3(a)]. When these results are compared to those for thin films where two new defects are found, i.e., a predominant level for electron trapping at 0.07 eV, assigned to In$_{Cu}$, and a new activation energy for hole trap at 0.155 eV assigned to Cu$_{In}^{II}$. These defects, which are related to the Cu–Au order, have the highest concentration and dominate the trapping process. These results support our previous conclusions and confirm that Cu–Au ordering is higher in a nanocomposite configuration compared to that in flat films. Like in flat films, as well as for 3D films, no influence of the filling duration on the emission rate has been observed.

Capture cross section of the minority and majority carriers determined by DLTS.

![FIG. 3. Activation energy of minority (a) and majority (b) charge traps in the subband gap of CuInS$_2$ that form nanocomposite heterojunctions.](Image)

<table>
<thead>
<tr>
<th>Sample morphology</th>
<th>Type of defects</th>
<th>Activation energy (eV)</th>
<th>Capture cross section (cm$^2$)</th>
<th>Density of traps (cm$^{-3}$)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Flat</td>
<td>Majority V$^+_{Cu}$</td>
<td>0.107</td>
<td>3.9 × 10$^{-17}$</td>
<td>5 × 10$^{13}$</td>
</tr>
<tr>
<td>Flat</td>
<td>Minority V$^+_{Cu}$</td>
<td>0.04</td>
<td>4.4 × 10$^{-16}$</td>
<td>1.8 × 10$^{13}$</td>
</tr>
<tr>
<td>Nanostructured</td>
<td>Majority Cu$<em>{In}^{II}$ or V$^-</em>{In}^{II}$</td>
<td>0.155</td>
<td>8 × 10$^{-15}$</td>
<td>2 × 10$^{14}$</td>
</tr>
<tr>
<td>Nanostructured</td>
<td>Majority V$^-_{Cu}$</td>
<td>0.1</td>
<td>7.2 × 10$^{-17}$</td>
<td>1 × 10$^{13}$</td>
</tr>
<tr>
<td>Nanostructured</td>
<td>Minority In$_{Cu}$</td>
<td>0.07</td>
<td>3.2 × 10$^{-17}$</td>
<td>1 × 10$^{14}$</td>
</tr>
</tbody>
</table>

To calculate the trap concentration, the net acceptor concentration ($N_A$-$N_D$) of the semiconductor, that forms the p-n heterojunctions, is measured using capacitance-voltage measurements. An effective $N_A$-$N_D$ concentration of 2 × 10$^{18}$ cm$^{-3}$ is found.

With DLTS, the influence of the geometry, i.e., flat films or nanocomposites on the electrical properties of the p-type CuInS$_2$, has been investigated. ALD-deposited CuInS$_2$ on the dense TiO$_2$ exhibits one electron-trap and one hole-trap center, at 0.04 eV and 0.1 eV, respectively. If CuInS$_2$ is deposited in a nanostructured matrix, the deep acceptor and donor concentrations become larger. The characteristic activation energy states related to the presence of Cu–Au disorder is observed in this case, i.e., a donor state localized at 0.07 eV and an acceptor state at 0.155 eV. Moreover, it is found that the activation energies do not depend on the duration of the filling pulse. These results are in line with our previous studies, but differ from other DLTS studies on CuInS$_2$.